Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications.

2. Features and benefits

- · High blocking voltage capability
- · Less sensitive gate for improved noise immunity
- · Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

3. Applications

- General purpose motor controls
- · General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
V_{DRM}	repetitive peak off-state voltage			6	300		V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 107 °C; Fig. 1; Fig. 2; Fig. 3	4			А	
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	25			А	
Symbol	Parameter	Conditions	Min Typ Max				Unit
Static ch	aracteristics		'	,			
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	5	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$		-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	11	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	30	70	mA

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		2
3	G	gate		T2 T1
mb	T2	mounting base; main terminal 2		sym051
			∐ ∐ ∐ 1 2 3	

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BT136-600	TO220	BT136-600,127	Tube	50	SOT78	13-Jun-2008
BT136-600/DG		BT136-600/DG,127	Tube	50	SOT78 (Halogen free)	13-Jun-2008

7. Marking

Table 4. Marking codes

Type number	Marking codes				
	Assembly factory: A	Assembly factory: d			
BT136-600	BT136 600 PJAxxx xx	-			
BT136-600/DG	BT136 600DG PJAxxx xx	BT136 600DG PJdxxx xx			

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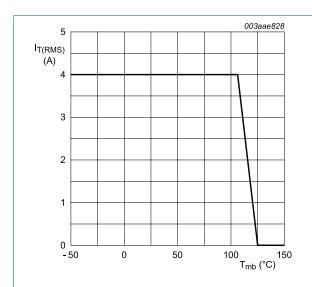
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 107 °C; Fig 1; Fig 2; Fig 3	4	А
I _{TSM} non-repetitive peak on- state current		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig 4; Fig 5	25	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	27	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN	3.1	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 70 mA; T2+ G+	50	A/µs
		I _G = 70 mA; T2+ G-	50	A/µs
		I _G = 70 mA; T2- G-	50	A/µs
		I _G = 140 mA; T2- G+	10	A/µs
I _{GM}	peak gate current		2	А
P_GM	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		125	°C

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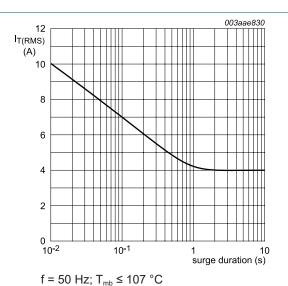
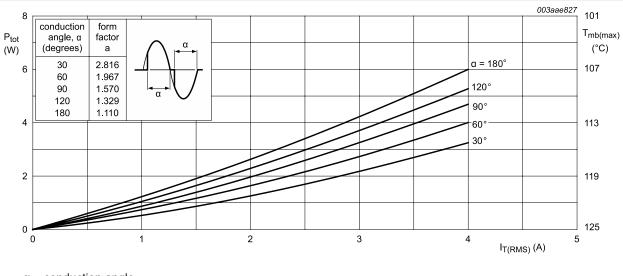


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

Fig. 2. RMS on-state current as a function of surge duration; maximum values



 α = conduction angle

a = form factor = $I_{T(RMS)}/I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

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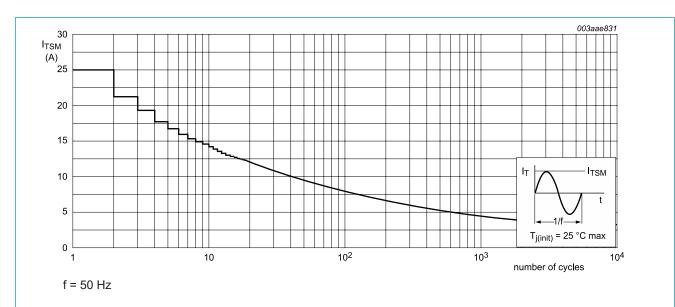
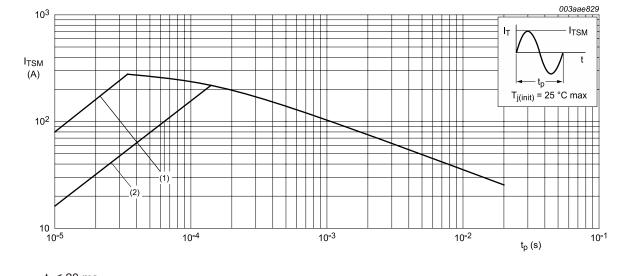


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



 $t_p \le 20 \text{ ms}$

 $(1) dI_T/dt limit$

(2) T2- G+ quadrant limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

4Q Triac

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)} thermal resistance		full cycle; Fig 6	-	-	3	K/W
	from junction to mounting base	half cycle; <u>Fig 6</u>	-	-	3.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

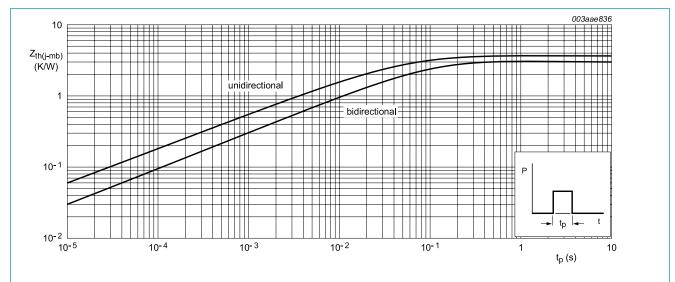


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

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10. Characteristics

Table 7. Characteristics

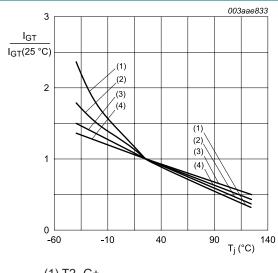
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics		·	,		
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	5	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;} $ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	11	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G+;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	30	70	mA
I _L latching current	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	7	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	16	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	5	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	7	30	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	5	15	mA
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics			,		
dV _D /dt	rate of rise of off-state voltage	e $V_{DM} = 402 \text{ V}; T_j = 125 ^{\circ}\text{C}; (V_{DM} = 67\% \text{ of } V_{DRM});$ exponential waveform; gate open circuit		250	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 95 ^{\circ}\text{C}; dI_{com}/dt = 1.8 \text{ A/}$ ms; $I_T = 4 \text{ A};$ gate open circuit	-	50	-	V/µs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 6 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ mA}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

3

2

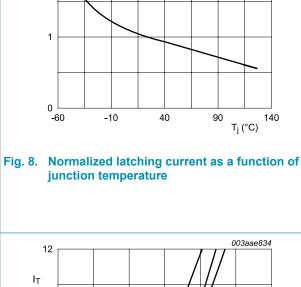
I_L I_{L(25°C)} **4Q Triac**

003aae835



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature



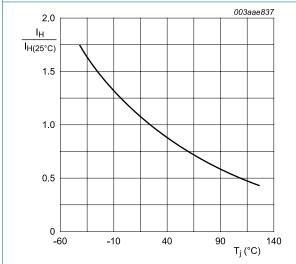
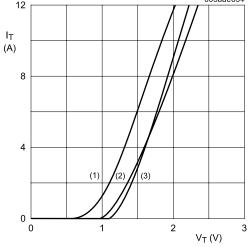


Fig. 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.27 \text{ V}; R_s = 0.091 \Omega$

(1) T_i = 125 °C; typical values

(2) T_i = 125 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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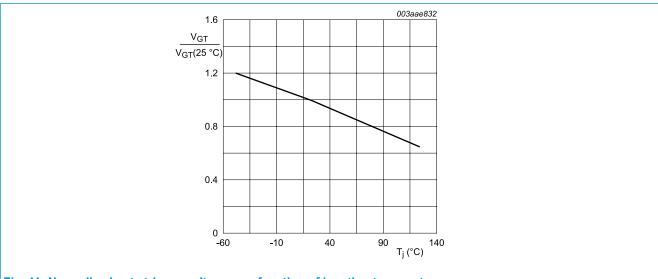


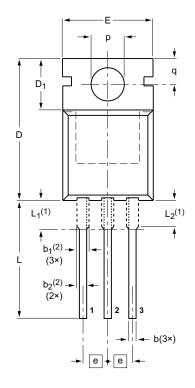
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

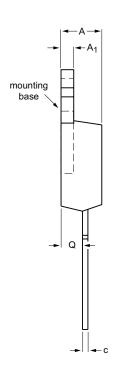
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11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78





0 5 10 mm

DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- $1. \ Lead \ shoulder \ designs \ may \ vary.$
- 2. Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

40 Triac

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- The term 'short data sheet' is explained in section "Definitions".
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4Q Triac

13. Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	6
10. Characteristics	7
11. Package outline	10
12. Legal information	
13. Contents	

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